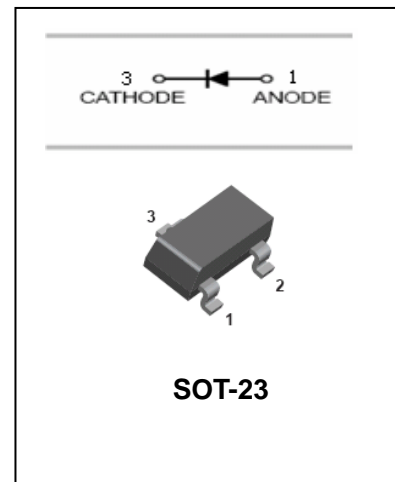


Schottky barrier diode

BAT750

FEATURES

- High conductance.
- Very low forward voltage drop.
- For use in DC-DC converter, PCMCIA, and mobile telecommunications application.



APPLICATIONS

- 0.75 Surface mount schottky barrier rectifier.

ORDERING INFORMATION

Type No.	Marking	Package Code
BAT750	K77	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Reverse Voltage	V_{RRM} V_{RWM} V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Rectified Current	I_O	750	mA
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load	I_{FSM}	5.5	A
Power Dissipation	P_d	350	mW
Typical Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	286	°C/W
Operating Junction Temperature Range	T_j	125	°C
Storage Temperature Range	T_{STG}	-40 to +125	°C



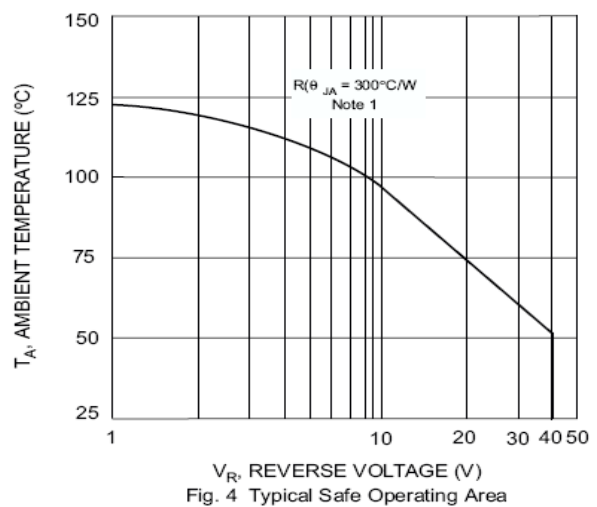
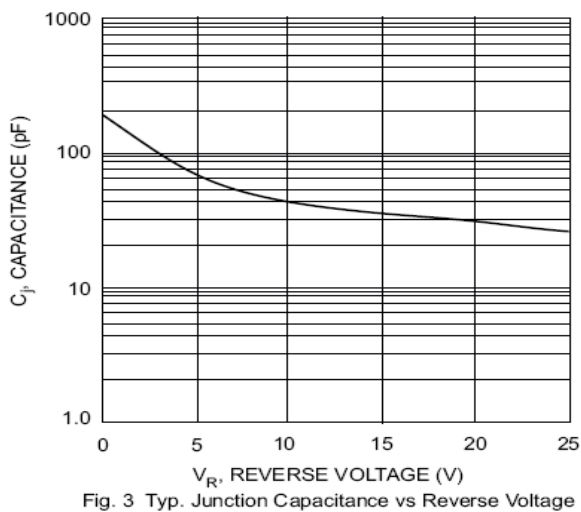
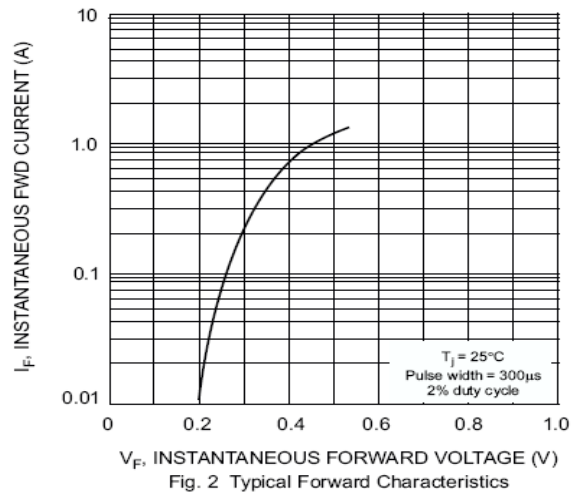
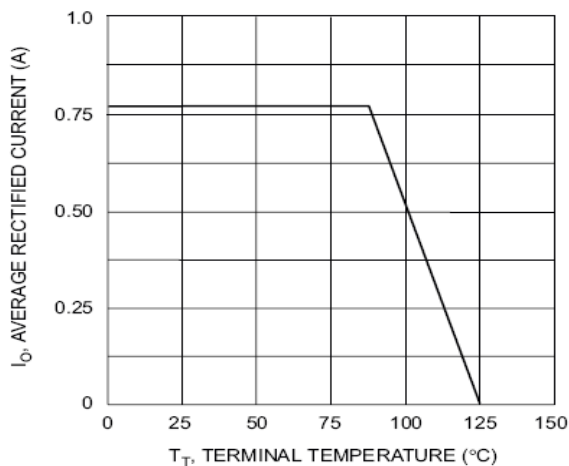
Schottky barrier diode

BAT750

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	MAX	UNIT	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	40	45	-	V	$I_R=300\mu A$
Forward Voltage	V_F	-	225	280	mV	$I_F=50mA$
			235	310		$I_F=100mA$
			290	350		$I_F=250mA$
			340	420		$I_F=500mA$
			390	490		$I_F=750mA$
			420	540		$I_F=1000mA$
			475	650		$I_F=1500mA$
Maximum Reverse Current	I_R	-	50	100	μA	$V_R=30V$
Junction Capacitance	C_j	-	175	-	μF	$V_R=0V, f=1.0MHz$
		-	25	-		$V_R=25V, f=1.0MHz$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Note: 1. Assumed application thermal conditions.
R θ_{JA} varies depending on application.

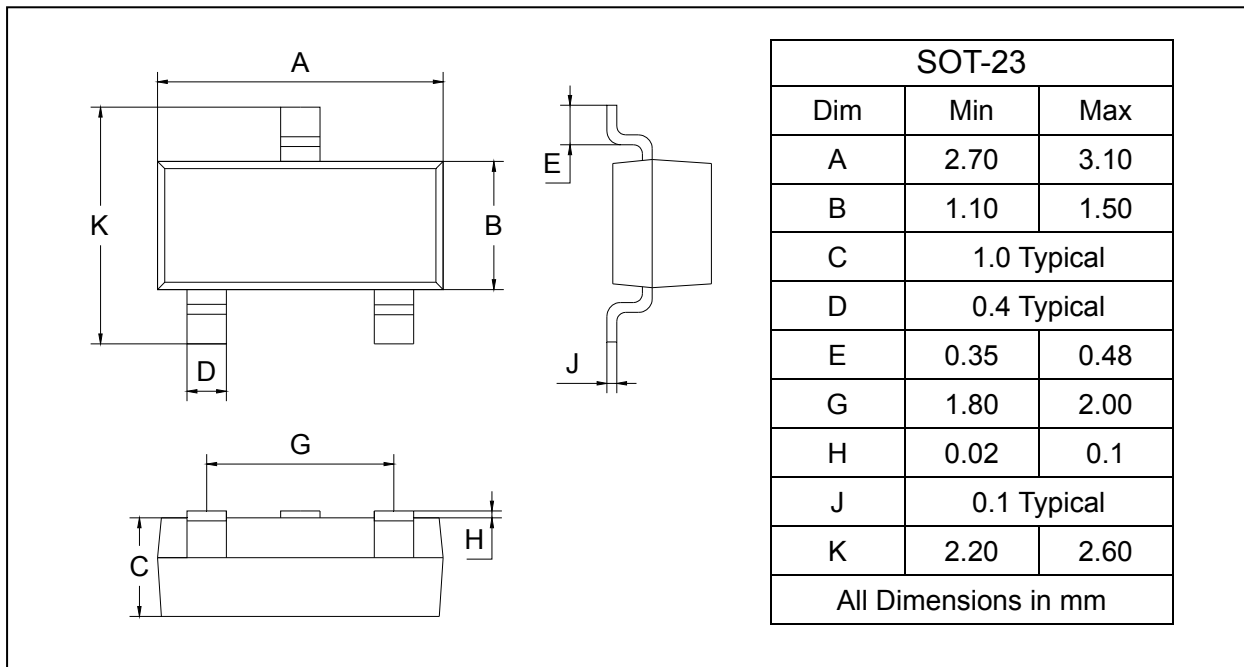
Schottky barrier diode

BAT750

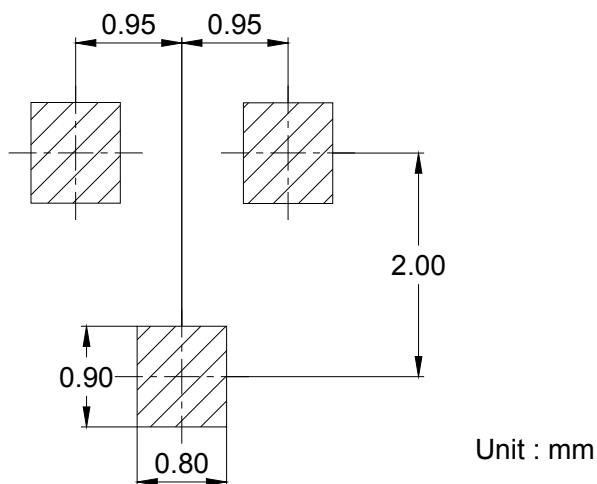
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAT750	SOT-23	3000/Tape&Reel